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VS-ST330CL

Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 650 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS IT(AV) 650 A VDRM/VRRM 400 V, 800 V, 1200 V, 1400 V, 1600 V VTM 1.90 V IGT 100 mA TJ -40 °C to +125 °C Package B-PUK (TO-200AC) Circuit configuration Single SCR

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC))
- High profile hockey PUK
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		650	A				
I _{T(AV)}	T _{hs}	55	°C				
1		1230	A				
I _{T(RMS)}	T _{hs}	25	°C				
1	50 Hz	9000	0				
I _{TSM}	60 Hz	9420	- A				
l ² t	50 Hz	405	– kA ² s				
1-1	60 Hz	370	KA-S				
V _{DRM} /V _{RRM}		400 to 1600	V				
t _q	Typical	100	μs				
TJ		-40 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE F	VOLTAGE RATINGS										
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA							
	04	400	500								
	08	800	900								
VS-ST330CL	12	1200	1300	50							
	14	1400	1500								
	16	1600	1700								

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COMPLIANT



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS	
Maximum average on-state current		180° condu	ction, half sine	wave	650 (314)	А	
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (75)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	1230		
		t = 10 ms	No voltage		9000		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		9420	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		7570		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	7920		
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	405	- kA ² s	
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		370		
	1-1	t = 10 ms	100 % V _{RRM}		287		
		t = 8.3 ms	reapplied		262		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	4050	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.91	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$				
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.57	mΩ	
High level value of on-state slope resistance	r _{t2}	$(l > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.57	11152	
Maximum on-state voltage	V_{TM}	$I_{pk} = 1730 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.90	V	
Maximum holding current	Ι _Η	T - 25 °C	anada ayanby 1	2. V registive lead	600	mA	
Typical latching current	١L	$i_{\rm J} = 25^{-1}$ C,	anoue supply 1	2 V resistive load	1000	IIIA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs				
Typical delay time t _d		Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	110				
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs				

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA			



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TRIGGERING						
PABAMETER	SYMBOL	TEST CONDITIONS			VALUES	
FARAMETER	STIVIDOL	TEX	ST CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10	0.0	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3	.0	А
Maximum peak positive gate voltage	$+V_{GM}$		t < 5 mc	2	20	v
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	v
	I _{GT}	T _J = -40 °C			-	
DC gate current required to trigger		T _J = 25 °C		100	200	mA
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-	
		T _J = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C			3.0	V
		T _J = 125 °C			-	
DC gate current not to trigger	I _{GD}	T T movimum	Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to +125	℃		
Maximum storage temperature range	T _{Stg}		-40 to +150			
Movimum thermal registence, junction to heataink	Р	DC operation single side cooled	0.11			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.06	K/W		
Maximum thermal registeres, ease to be tainly	Р	DC operation single side cooled	0.011	r∨ vv		
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation double side cooled	0.005			
Mounting force, ± 10 %			9800 (1000)	N (kg)		
Approximate weight			250	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION RECTANGULAR CONDUCTION				TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TESTCONDITIONS	UNITS		
180°	0.012	0.010	0.008	0.008				
120°	0.014	0.015	0.014	0.014				
90°	0.018	0.018	0.019	0.019	$T_J = T_J$ maximum	K/W		
60°	0.026	0.027	0.027	0.028				
30°	0.045	0.046	0.046	0.046				

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

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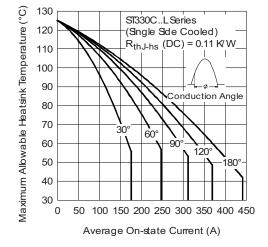


Fig. 1 - Current Ratings Characteristics

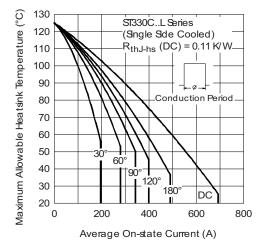


Fig. 2 - Current Ratings Characteristics

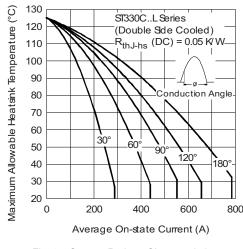


Fig. 3 - Current Ratings Characteristics

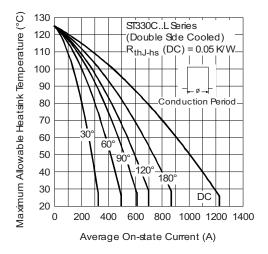


Fig. 4 - Current Ratings Characteristics

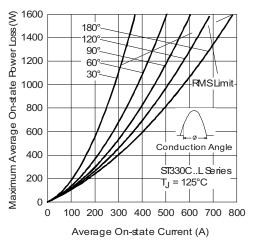
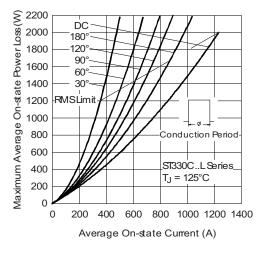
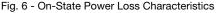


Fig. 5 - On-State Power Loss Characteristics





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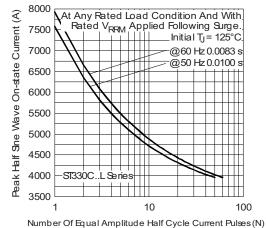
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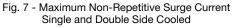
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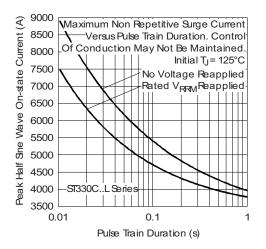
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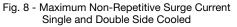
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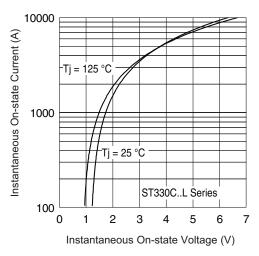




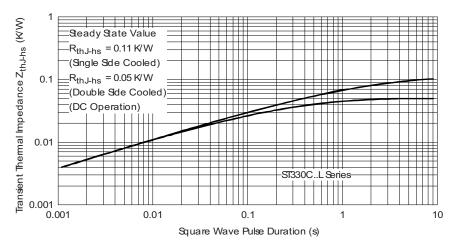


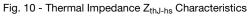












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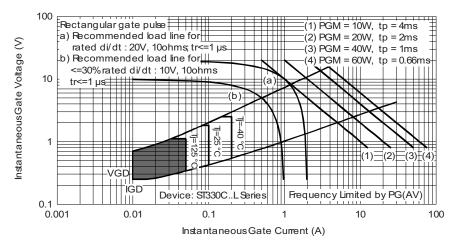


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	33	0	С	16	L	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -	Visl	nay Sen	niconduo	ctors pro	oduct				
	2 -	Thy	ristor							
	3 -	Ess	ential p	art numl	ber					
	4 -	0 =	convert	er grade	9					
	5 -	C =	cerami	DUK						
	6 -	Vol	Voltage code x 100 = V _{RRM} (see Voltage Ratings table)							
	7 -	L =	L = PUK case B-PUK (TO-200AC)							
	8 -	0 =	0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)							
		1 =	1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)							
		2 =	eyelet t	erminals	s (gate a	nd auxi	liary ca	thode s	oldered leads)	
		3 =	fast-on t	erminals	(gate ar	nd auxilia	ary cath	ode sold	lered leads)	
	9 -		ical dV/		-		-			
					= 1000 V	-	-			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95076				

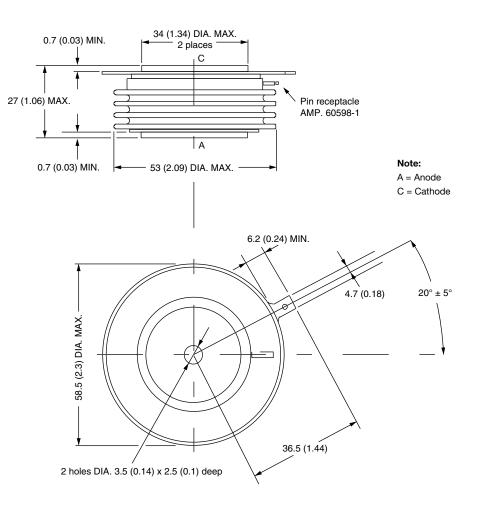
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B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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Revision: 01-Jan-2025

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